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AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A fabrication method of a liquid crystal display device, comprising:

forming a gate line on a substrate by applying a gate photoresist pattern by printing;

sequentially forming a gate insulating layer, a semiconductor layer, and a high-concentrated N+ layer over the gate line;

forming an active region including the high-concentrated N+ layer by applying an active photoresist pattern by printing, wherein the active region is formed by sequentially removing the high-concentrated N+ layer and the semiconductor layer using the active photoresist pattern formed by printing as a mask;

removing the active photoresist pattern;

forming a conductive layer over the active region;

depositing a photoresist layer over the conductive layer;

applying a mask in the photoresist layer, and performing a lithography process, ~~and thereby forming a source/drain electrode~~ to form a photoresist layer pattern;

sequentially removing the conductive layer including the high-concentrated N+ layer above the channel region by using the photoresist layer pattern as a mask to a source/drain electrode;

forming a passivation layer over the source/drain electrode;

forming a contact hole over the passivation layer by applying a contact hole photoresist pattern by printing; and

forming a pixel electrode on the passivation layer by printing a pixel electrode photoresist

pattern.

2. (Original) The method of claim 1, wherein the mask includes a channel region pattern.

3. (Previously Presented) The method of claim 1, wherein the printing is roller printing.

4. (Canceled).

5-14. (Cancelled)

15. (Previously Presented) The method of claim 1, wherein the mask applied over the photoresist layer in the step of applying the mask is the only mask applied through out the method of claim 1.

16. (Previously Presented) The method of claim 1, wherein the printing is ink jet printing.

17 - 19. (Canceled)

20. (Currently Amended) A method for forming a liquid crystal display device, comprising:

forming a gate line on a substrate, wherein the step of forming the gate line includes applying a gate photoresist pattern on the substrate by printing;

removing the gate photoresist pattern;

forming a gate insulating layer, a semiconductor layer, and an impurity-doped layer over

the gate line;

forming an active region including the impurity-doped layer;

forming a conductive layer over the active region;

depositing a photoresist layer over the conductive layer;

applying a mask over the photoresist layer, patterning the photoresist layer using the mask;

forming source and drain electrodes using the patterned photoresist layer;

removing the patterned photoresist layer;

~~patterning the conductive layer using the patterned photoresist layer to form~~forming a source electrode and a drain electrode over the active region;

forming a passivation layer over the source and drain electrodes;

forming a contact hole in the passivation layer by applying a contact hole photoresist pattern by printing; and

forming a pixel electrode on the passivation layer by printing a pixel electrode photoresist pattern.

21. (Previously Presented) The method of claim 20, wherein the mask applied over the photoresist layer in the step of applying the mask is the only mask applied through out the method of claim 20.

22. (Canceled)

23. (Previously Presented) The method of claim 20, wherein the step of forming the active region includes applying an active photoresist pattern including the impurity-doped layer by printing.